

## Plastic-Encapsulate Diodes

Schottky Barrier Diode

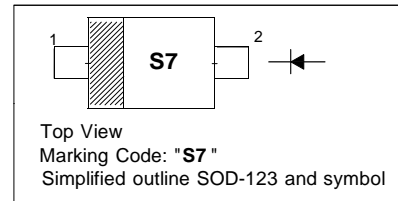
### FEATURES

- Small power mold type.
- Low IR
- High reliability.
- Silicon epitaxial planar

**Marking: S7**

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	VRM	40	V
Reverse voltage (DC)	VR	40	V
Average rectified forward current	IO	1	A
Forward current surge peak (60Hz · 1cyc)	IFSM	5.5	A
Junction temperature	TJ	150	°C
Storage temperature range	TSTG	-40 ~ +150	°C

### THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Power Dissipation	PD	400	mW
Thermal Resistance,Junction-to-Ambient	RθJA	312	°C/W
Thermal Resistance,Junction-to-Case	RθJC	150	°C/W

### ELECTRICAL CHARACTERISTICS (Ta= 25°C )

Characteristic	Symbol	Min	Typ.	Max	Unit
Forward voltage (IF = 1.0 A)	VF	-	0.54	0.56	V
Reverse current (VR=40V)	IR	-	-	30	μA

## Typical Characteristics

